

45. (Amended) The ceramics fabrication device as defined in claim 41, wherein the base of the substrate functions as the heating section.

46. (Amended) The ceramics fabrication device as defined in claim 41, wherein at least one of the active species feeder and the electromagnetic wave generating section feeds at least one of the active species and the electromagnetic wave to part of the substrate.

50. (Amended) A semiconductor device comprising a capacitor which includes a dielectric film formed by the fabrication method as defined in claim 1.

51. (Amended) A piezoelectric device comprising a dielectric film formed by the fabrication method as defined in claim 1.

REMARKS

Claims 1-51 are pending. Claims 35, 37, 39, 40, 45, 46, 50 and 51 are amended to eliminate multiple dependencies. Prompt and favorable consideration on the merits is respectfully requested.

The attached Appendix includes marked-up copies of each rewritten claim (37 C.F.R. §1.121(c)(1)(ii)).

Respectfully submitted,



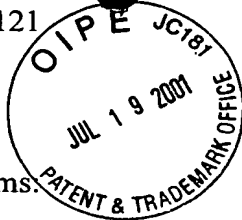
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Attached: APPENDIX
Date: July 19, 2001

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APPENDIX

Changes to Claims:

The following are marked-up versions of the amended claims:

35. (Amended) The method of fabricating ceramics as defined in claim 1, ~~3, 15, 23~~
~~or 25~~,

wherein at least one of the active species and the electromagnetic wave is fed to part
of a substrate.

37. (Amended) The method of fabricating ceramics as defined in claim 3, ~~15 or~~
~~25~~,

wherein the first ceramic film is formed by a coating method, the liquid source
mist chemical deposition (LSMCD), the chemical vapor deposition (CVD), or a sputtering
method.

39. (Amended) The method of fabricating ceramics as defined in claim 1, ~~3, 15, 23~~
~~or 25~~,

wherein the ceramic film or the second ceramic film is formed of ferroelectrics.

40. (Amended) The method of fabricating ceramics as defined in claim 1, ~~3, 15, 23~~
~~or 25~~,

wherein the ceramic film or the second ceramic film is formed at a temperature of
less than 600°C.

45. (Amended) The ceramics fabrication device as defined in claim 41 ~~or 43~~,
wherein the base of the substrate functions as the heating section.

46. (Amended) The ceramics fabrication device as defined in claim 41 ~~or 43~~,
wherein at least one of the active species feeder and the electromagnetic wave
generating section feeds at least one of the active species and the electromagnetic wave to part
of the substrate.

50. (Amended) A semiconductor device comprising a capacitor which includes a dielectric film formed by the fabrication method as defined in claim 1 ~~any one of claims 1 to 40~~.

51. (Amended) A piezoelectric device comprising a dielectric film formed by the fabrication method as defined in claim 1 ~~any one of claims 1 to 40~~.